

Beamtest of novel n-in-p strip sensors for very high radiation environment

Tuesday 4 September 2012 15:20 (1 hour)

Results on a beam test of n-in-p silicon strip sensors aimed for the ATLAS SCT(Semi-Conductor Tracker) upgrades for High Luminosity LHC(HL-LHC) are presented. This Beam test was operated with a new DAQ system consisting of a universal read-out board called 'SEABAS' and a beam tracking system with the spacial resolution less than 5 micro meters, and held at RCNP in December 2011. Behaviors of the new 1 cm x 1 cm n-in-p miniature sensors before and after irradiation up to 10^{15} n_eq/cm² are discussed. Collected charge of non-irradiated is sensor is 6fC at full depletion voltage, while of 10^{15} n_eq/cm² irradiated sensor is 4.2fC. The effective region on the strip edges around PTP structures of the non-irradiated sensor reached to the bias rail, while of the 10^{15} n_eq/cm² irradiated sensor it reached only up to strip edges.

Primary author: KUBOTA, Tomonori (Tokyo Institute of Technology (JP))

Co-author: SILICON, collaboration ATLAS-Japan (JP)

Presenter: KUBOTA, Tomonori (Tokyo Institute of Technology (JP))

Session Classification: Poster session

Track Classification: Particle physics applications - High Energy Physics